## **NCE N-Channel Super Trench Power MOSFET**

#### **Description**

The NCEP01T13BD uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

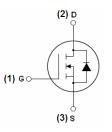
#### **General Features**

- V<sub>DS</sub> =100V,I<sub>D</sub> =135A
  - $R_{DS(ON)}$  <4.3m $\Omega$  @  $V_{GS}$ =10V
  - $R_{DS(ON)}\!<\!\!5m\Omega$  @  $V_{GS}\!=\!4.5V$
- Excellent gate charge x R<sub>DS(on)</sub> product
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

### **Application**

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED! 100% ΔVds TESTED!



#### Schematic diagram



Marking and pin assignment



TO-263-2L top view

#### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP01T13BD	NCEP01T13BD	TO-263-2L	-	-	-

#### Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	100	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous (Silicon Limited)	I <sub>D</sub>	150	Α
Drain Current-Continuous (Package Limited)	I <sub>D</sub>	135	Α
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	108	Α
Pulsed Drain Current	I <sub>DM</sub>	500	Α
Maximum Power Dissipation	P <sub>D</sub>	220	W
Derating factor		1.5	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	1156	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 175	$^{\circ}$ C



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#### **Thermal Characteristic**

Electrical Characteristics (T<sub>C</sub>=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	· ·					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	100		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)	· ·					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1.0	1.9	3.0	V
Drain Course On Ctate Desistance	В	V <sub>GS</sub> =10V, I <sub>D</sub> =60A	-	3.7	4.3	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =60A	-	4.3	5.0	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =10V,I <sub>D</sub> =60A	70	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	\/ -50\/\/ -0\/	-	10900	-	PF
Output Capacitance	Coss	$V_{DS}$ =50V, $V_{GS}$ =0V, F=1.0MHz	-	840	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	r=1.0lvln2	-	36	-	PF
Switching Characteristics (Note 4)	·					
Turn-on Delay Time	t <sub>d(on)</sub>		-	25	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =50 $V$ , $I_D$ =60 $A$	-	92	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{G}$ =4.7 $\Omega$	-	62	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	21	-	nS
Total Gate Charge	Qg	\/ F0\/   C0A	-	150		nC
Gate-Source Charge	$Q_{gs}$	$V_{DS}=50V, I_{D}=60A,$	-	38		nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V		17.8		nC
Drain-Source Diode Characteristics			•			•
Diode Forward Voltage (Note 3)	$V_{SD}$	V <sub>GS</sub> =0V,I <sub>S</sub> =135A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	135	Α
Reverse Recovery Time	t <sub>rr</sub>	$T_J = 25^{\circ}C$ , $I_F = I_S$	-	75		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	165		nC

#### Notes:

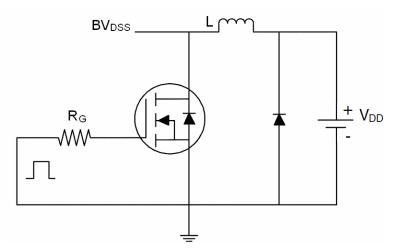
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\text{C}$  ,V\_DD=50V,V\_G=10V,L=0.5mH,Rg=25 $\Omega$



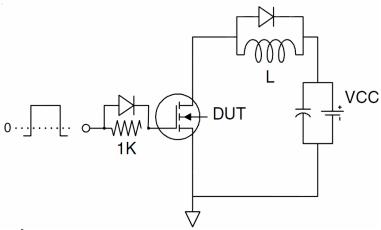
# NCEP01T13BD

#### **Test Circuit**

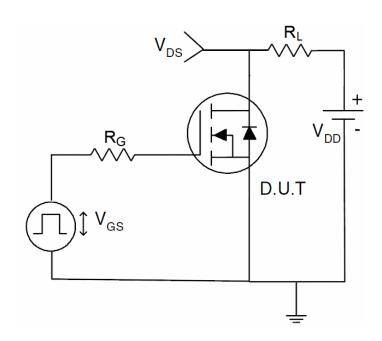
## 1) E<sub>AS</sub> test Circuit



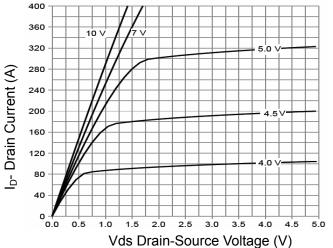
## 2) Gate charge test Circuit



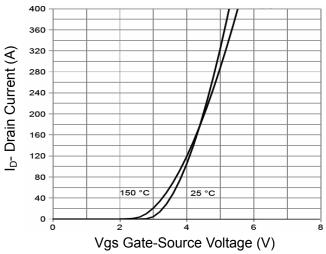
## 3) Switch Time Test Circuit







**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

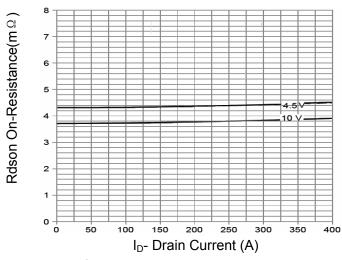


Figure 3 Rdson- Drain Current

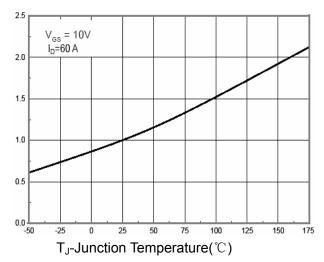


Figure 4 Rdson-JunctionTemperature

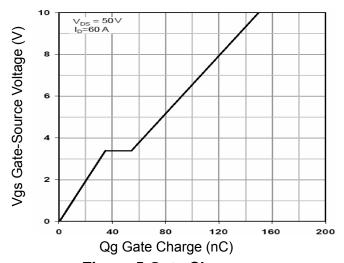


Figure 5 Gate Charge

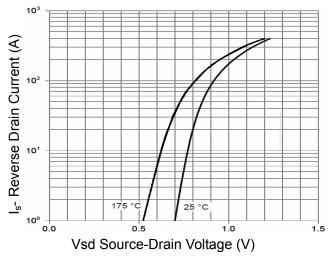


Figure 6 Source- Drain Diode Forward



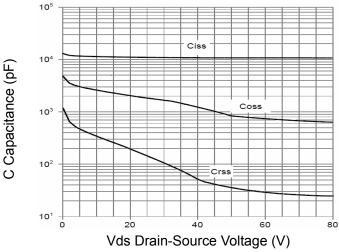


Figure 7 Capacitance vs Vds

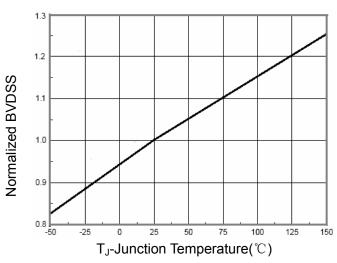
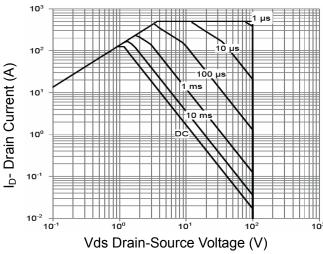


Figure 9 BV<sub>DSS</sub> vs Junction Temperature



**Figure 8 Safe Operation Area** 

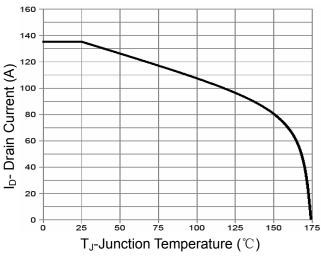
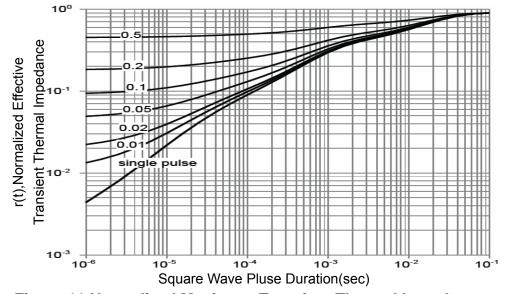


Figure 10 Current De-rating

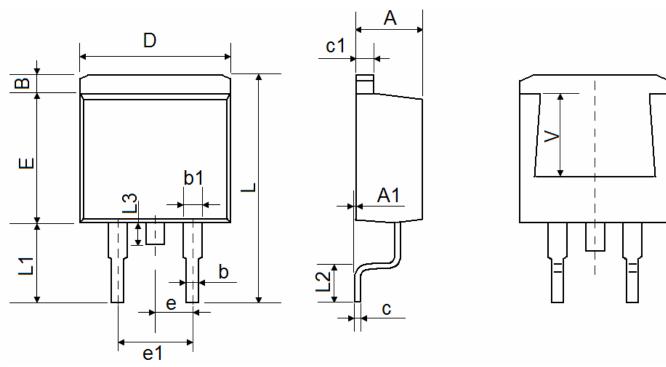


**Figure 11 Normalized Maximum Transient Thermal Impedance** 





## **TO-263-2L Package Information**



Cumbal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.470	4.670	0.176	0.184	
A1	0.000	0.150	0.000	0.006	
В	1.170	1.370	0.046	0.054	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
E	8.500	8.900	0.335	0.350	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
L	15.050	15.450	0.593	0.608	
L1	5.080	5.480	0.200	0.216	
L2	2.340	2.740	0.092	0.108	
L3	1.300	1.700	0.051	0.067	
V	5.600 REF		0.220 REF		



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